

SPD61089

High Voltage Ringing SLIC Protector

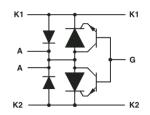
Waveshape	
10/700us	50A
10/1000us	40A

Descriptions

This device is especially designed to protect Subscriber Line Interface Circuit (SLIC) against transient overvoltage. Positive overloads are clipped with 2 diodes. Negative surges are suppressed by 2 Thyristors, their breakdown voltage being referenced to VBAT through the gate. This component presents a very low gate triggering current and minimizes overvoltage stress on the SLIC.

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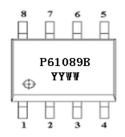


Package & Device Symbol

K1	le	8	_ K1
G	2	7	A
	3	6	A
K2	4	5	_K2

Pin configuration (Top view)

Pin #	Pin Name	Description		
1, 4, 5, 8	K1, K2	Connect to subscriber lines (Tip/Ring)		
2	G	Connect to battery (Reference Voltage)		
6, 7	А	Connect ground		
3	NC	Not connected		



P61089B = Device Code

Y	= Special Code
Y	= Special Code

Y =Year

WW =Week

Marking

Order information

Device	Package	Shipping
SPD61089-8/TR	SOP-8L	4000/Reel&Tape

Features

- Dual programmable transient suppressor
- Wide battery voltage supports
- Low gate triggering current
- High holding current.
- MSL: Level 3

Applications

- Switch Line Card
- Access Network Line Card
- PBX
- VolP

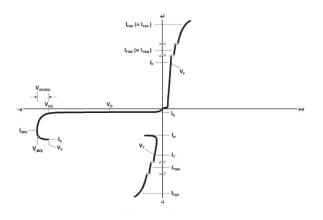


Absolute Maximum ratings

Parameter		Symbol	Value	Unit
	10/1000us (Telcordia (Bellcore) GR-1089-CORE, Issue 3.)		40	
Non-repetitive peak on-state	5/310us (ITU-T K.20, K.21& K.45, K.44 open-circuit voltage wave shape 10/700 µs)	I _{PPSM}	50	А
pulse current	2/10us (Telcordia (Bellcore) GR-1089-CORE, Issue 3)		120	
	0.1s		6.5	
Non repetitive	1s		4.5	
peak on-state current	5s	ITSM	2.4	А
(sinusoidal) 60Hz	30s		1.3	
	900s		0.72	
Re	petitive peak off-state voltage, $V_{GK}=0$	V _{DRM}	-170	V
Repe	titive peak gate-cathode voltage, $V_{KA}=0$	V _{GKRM}	-167	V
0	Operating free-air temperature range		-40-85	°C
Storage temperature range		T _{STG}	-40-150	°C
Junction temperature		TJ	-40-150	°C
Maximum lead temperature for soldering during 10s		T∟	260	°C
Ju	nction to free air thermal resistance	R $_{ m JA}$	120	°C /W

Parameter Measurement Information

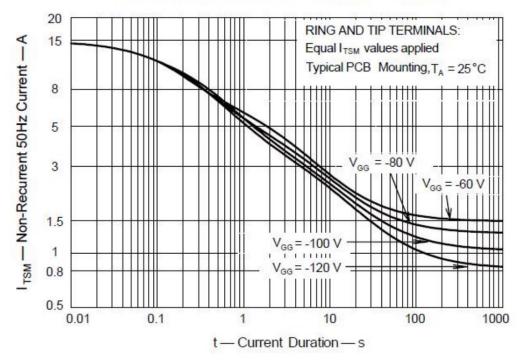
Parameter	Symbol
Off-state current	I _D
Holding current	Ι _Η
Breakover voltage	V _(BO)
Forward voltage	V _F
Peak forward recovery voltage	V _{FRM}
Gate-cathode impulse breakover voltage	V _{GK(BD)}
Gate reverse current	I _{GKS}
Gate trigger current	I _{GT}
Gate-cathode trigger voltage	V _{GT}
Cathode-anode off-state capacitance	Ска



Electronics Characteristics (Ta=25°C, unless otherwise noted)

Parameter Symbol Test Conditions		Min	Тур	Max	Unit	
Forward voltage	V _F	I _F =5A, t _w =200us			3	V
Impulse peak forward recovery voltage	V _{FRM}	2/10us, I _F =100A, R _s =50 Ω , di/dt=80A/us			10	V
Off-state current	Ι _D	V _D = -170V, V _{GK} =0, T _J = 25 °C			-5	uA
	D	V _D = -170V, V _{GK} =0, T _J = 85 °C			-ə	uA
Impulse breakover voltage	V _(BO)	2/10us, I _™ =100A, R _s =50Ω di/dt=-80A/us, V _{GG} =-100V			-112	V
Holding current	I _H	I_{T} =-1A, di/dt=1A/ms, V _{GG} =-100V	-150			mA
Gate reverse current		$V_{GG}=V_{GK}=$ -167V, $V_{KA}=0$, $T_{J}=25$ °C			-5	
Gate reverse current	I _{GAS}	V _{GG} =V _{GK} = -167V, V _{KA} =0, T _J = 85 °C		-5	uA	
Gate trigger current	I _{GT}	I _⊤ =3A, t _{p(g)} ≥20us, V _{GG} =-100V			5	mA
Gate trigger voltage	V _{GT}	I _⊤ =3A, t _{p(g)} ≥20us, V _{GG} =-100V			2.5	V
	<u> </u>	$f=1MHz, V_D=1V, I_G=0, V_D=-3V$			110	
Anode-cathode offstate capacitance	Ска	$f=1MHz, V_{D}=1V, I_{G}=0, V_{D}=-48V$			55	pF

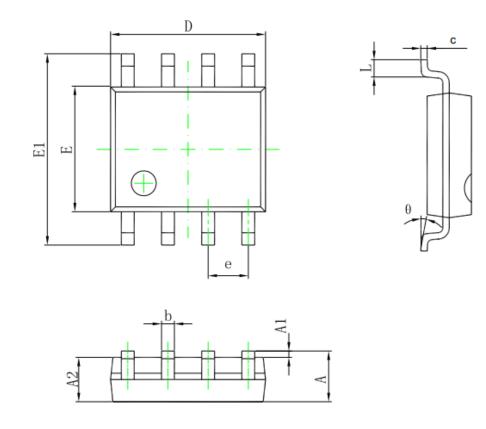
Non-Repetitive Peak On-state Current against Duration





Package outline dimensions

SOP-8L

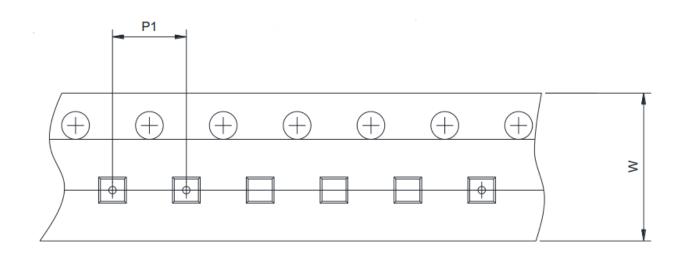


Cumb a 1	Dimensions In Millimeters (mm)				
Symbol	Min.	Тур.	Max.		
А	1.35	1.55	1.75		
A1	0.05	0.15	0.25		
A2	1.25	1.40	1.65		
b	0.33	-	0.51		
с	0.17	-	0.26		
D	4.70	4.90	5.10		
Е	3. 70	3.90	4.10		
E1	5.80	6.00	6.20		
е		1.27 BSC			
L	0.40	-	1.27		
θ	0°	-	8°		

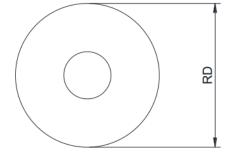
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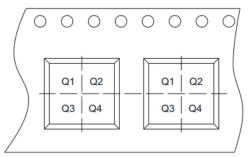
Tape Dimensions



Reel Dimensions



Quadrant Assignments For PIN1 Orientation In Tape





User Direction of Feed

RD	Reel Dimension	🗌 7inch	✓ 13inch		
W	Overall width of the carrier tape	🗖 8mm	✓ 12mm		
P1	Pitch between successive cavity centers	🗌 2mm	4mm	✓ 8mm	
Pin1	Pin1 Quadrant	✓ Q1	🗌 Q2	🗌 Q3	□ Q 4

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